

CLAIMS

1. A hot plate for a semiconductor producing/examining device,
comprising a resistance heating element formed on a surface of
5 a ceramic substrate or inside the ceramic substrate,
wherein the glossiness of the heating face of said ceramic
substrate is 1.5 % or more.
2. The hot plate for a semiconductor producing/examining
10 device according to claim 1,
wherein said ceramic substrate contains 0.5 to 10 weight %
of oxygen.
3. The hot plate for a semiconductor producing/examining
15 device according to claim 1 or 2,
wherein said ceramic substrate is subjected to an annealing
treatment.
4. The hot plate for a semiconductor producing/examining
20 device according to any of claims 1 to 3,
wherein said ceramic substrate is subjected to a cold
isostatic pressing process before it is sintered.